

RS0806A/RS0806B Series 8A TRIACs
DESCRIPTION:

High current density due to double mesa technology, SIPOS and Glass Passivation.

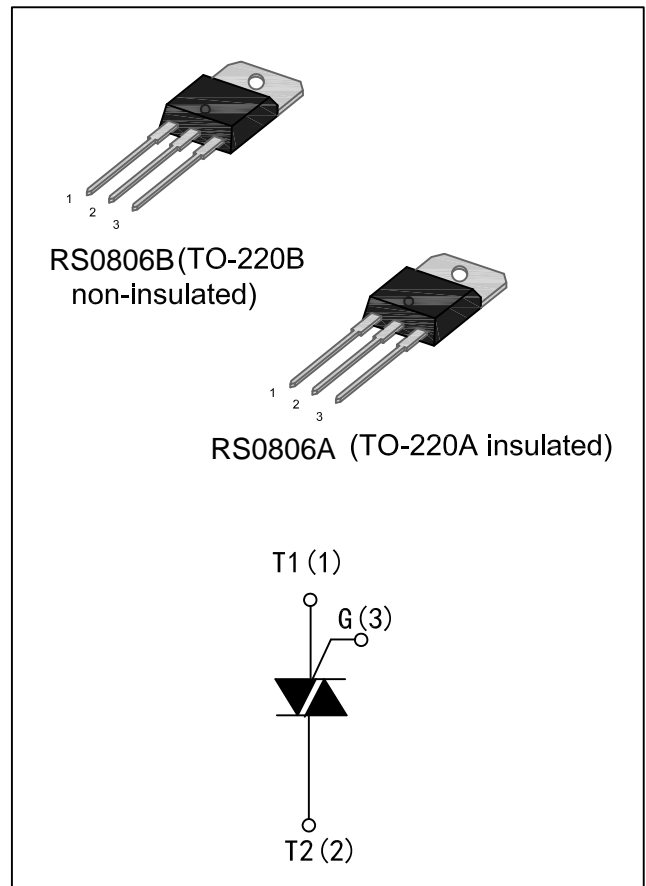
RS0806A/B series triacs is suitable for general purpose AC switching, They can be used as an ON/OFF function in applications such as static relays, heating regulation, induction motor starting circuits...or for phase control operation, light dimmers, motor speed controllers.

RS0806A/B-SW -CW -BW are 3 quadrants triacs, They are specially recommended for use on inductive loads.

RS0806A are isolated in internal, they provide a 2500V RMS isolation voltage from all three terminals to external heat sink.

MAIN FEATURES

Symbol	Value	Unit
IT(RMS)	8	A
VDRM/VRRM	600 and 800	V
V _{TM}	1.55	V


ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40 to +150	°C
Operating junction temperature range	T _j	-40 to +125	°C
Repetitive Peak Off-state Voltage	T _j =25°C	V _{DRM}	600and800
Repetitive Peak Reverse Voltage	T _j =25°C	V _{RRM}	600and800
Non repetitive Surge Peak Off-state Voltage	tp=10ms, T _j =25°C	V _{DSM}	700and900
Non repetitive Peak Reverse Voltage		V _{RSM}	700and900
RMS on-state current (full sine wave)	JST08B T _c =110°C	I _T (RMS)	8
	JST08A T _c =100°C		
Non repetitive surge peak on-state current (full cycle, T _j =25°C)	f = 60 Hz t=16.7ms	I _{TSM}	84
	f = 50 Hz t=20ms		80
I ² t Value for fusing	tp=10ms	I ² t	36
Critical rate of rise of on-state current (I _G =2×I _{GT} , tr≤100 ns, f=120Hz, T _j =125°C)	di / dt	50	A/μs
Peak gate current (tp=20us, T _j =125°C)	I _{GM}	4	A
Peak Gate Power Dissipation (tp=20us, T _j =125°C)	P _{GM}	10	W
Average gate power dissipation (T _j =125°C)	P _{G(AV)}	1	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

● 3 Quadrants

Symbol	Test Condition	Quadrant		RS0806A/RS0806B				Unit
				TW	SW	CW	BW	
I _{GT}	V _D =12V R _L =33Ω	I-II-III	MAX.	5	10	35	50	mA
V _{GT}		I-II-III	MAX.	1.3				V
V _{GD}	V _D =V _{DRM} R _L =3.3KΩ T _j =125°C	I-II-III	MIN.	0.2				V
I _L	I _G =1.2I _{GT}	I-III	MAX.	15	20	50	70	mA
		II	MAX.	25	35	60	80	mA
I _H	I _T =100mA		MAX.	10	15	40	60	mA
dV/dt	V _D =67%V _{DRM} gate open T _j =125°C		MIN.	20	40	400	1000	V/μs
(dV/dt) _c	(dI/dt) _c =3.5A/ms T _j =125°C		MIN.	0.5	1	10	25	V/μs

● 4 Quadrants

Symbol	Test Condition	Quadrant		RS0806A/RS0806B		Unit
				C	B	
I _{GT}	V _D =12V R _L =33Ω	I-II-III IV	MAX.	25 50	50 100	mA
V _{GT}		ALL	MAX.	1.3		V
V _{GD}	V _D =V _{DRM} R _L =3.3KΩ T _j =125°C	ALL	MIN.	0.2		V
I _L	I _G =1.2I _{GT}	I-III-IV	MAX.	35	50	mA
		II	MAX.	60	80	mA
I _H	I _T =100mA		MAX.	25	50	mA
dV/dt	V _D =67%V _{DRM} gate open T _j =125°C		MIN.	200	400	V/μs
(dV/dt) _c	(dI/dt) _c =3.5A/ms T _j =125°C		MIN.	5	10	V/μs

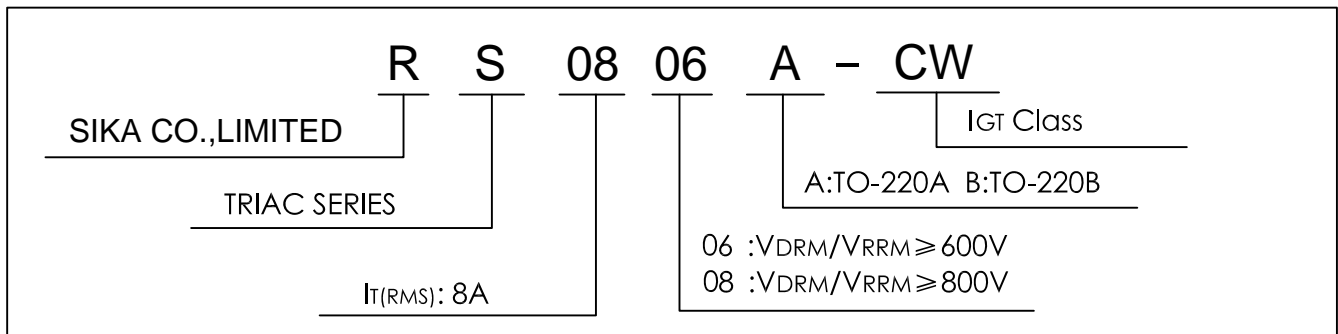
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =11A, t _p =380μs	T _j =25°C	1.55	V
I _{DRM} I _{RRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	5	μA
		T _j =125°C	1	mA

THERMAL RESISTANCES

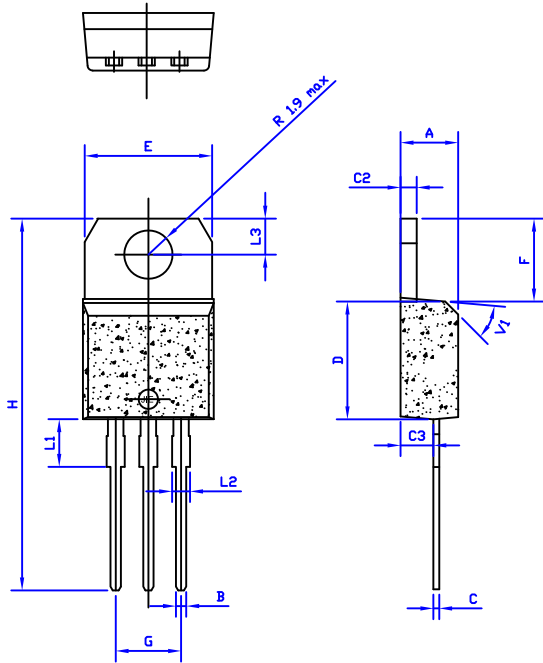
Symbol	Parameter		Value	Unit
R _{th(J-C)}	Junction to Case(AC)	JST08B	1.6	°C/W
		JST08A	2.5	
R _{th(j-a)}	Junction to ambient (S=1cm ²)	JST08A	60	°C/W
		JST08B	60	

ORDERING INFORMATION



PACKAGE MECHANICAL DATA

TO-220A insulated package and TO-220B non-insulated package



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		1.181
B	0.61		0.88	0.024		0.034
C	0.46		0.70	0.018		0.027
C2	1.23		1.32	0.048		0.051
C3	2.4		2.72	0.094		0.107
D	8.6		9.7	0.338		0.382
E	9.8		10.4	0.386		0.409
F	6.2		6.6	0.244		0.259
G	4.8		5.4	0.189		0.213
H	28.0		29.8	11.0		11.7
L1		3.75			0.147	
L2	1.14		1.7	0.044		0.066
L3	2.65		2.95	0.104		0.116
V1		40°			40°	

Marking:

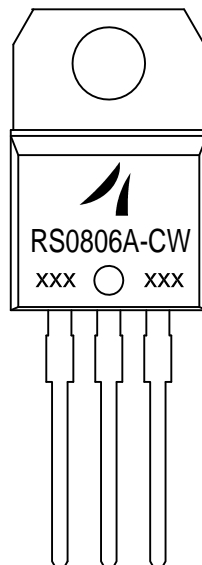


FIG.1:Maximum power dissipation versus RMS on-state current(full cycle)

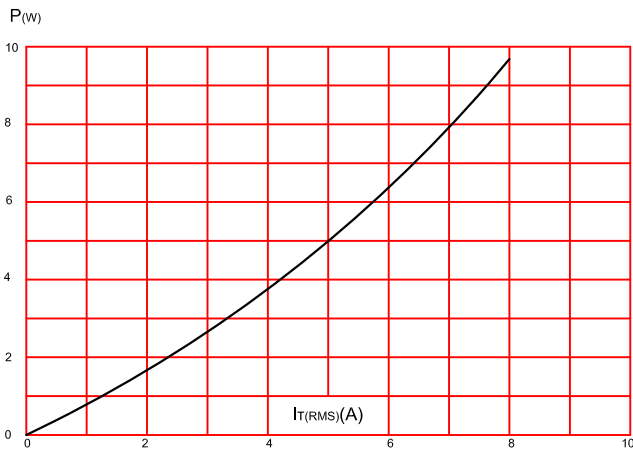


FIG.2:RMS on-state current versus case temperature(full cycle)

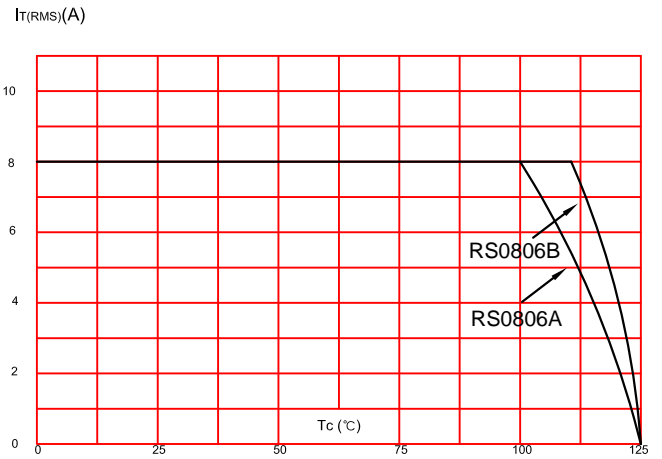


FIG.3:On-state characteristics (maximum values).

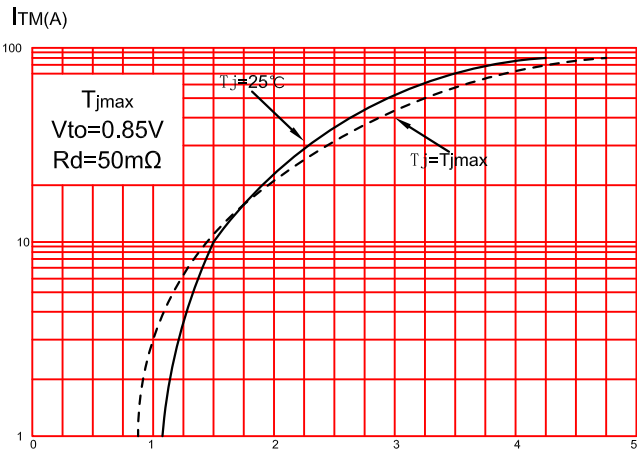


FIG.4:Surge peak on-state current versus number of cycles.

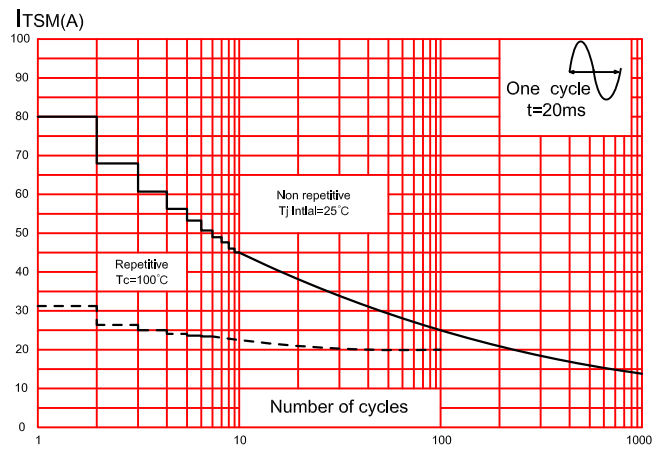


FIG.5:Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$, and corresponding value of I^2t .

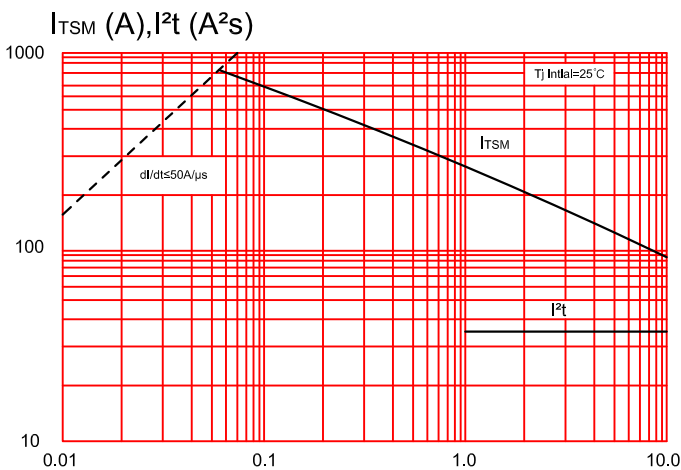
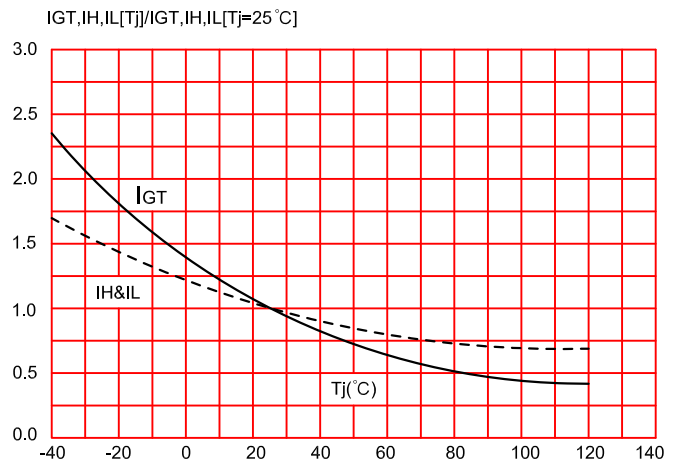


FIG.6:Relative variations of gate trigger current,holding current and latching current versus junction temperature(typical values)



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